



High Voltage Trench Schottky Diode

FEATURES

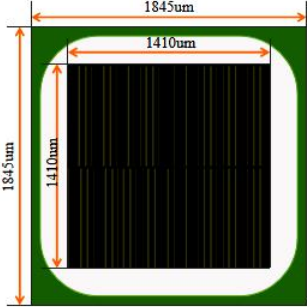
- Trench MOS Schottky technology
- Die in 6" Wafer Form
- 80V, 10A*
- $V_F=0.61V(\text{typ.})^{**}$

Electrical Characteristics (T_j=25°C)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V _{RRM}	Maximum repetitive peak reverse voltage	80	91	—	V	I _R = 500μA
V _F	Static Forward Voltage	—	0.40	0.44	V	I _F = 1A
		—	0.51	0.56	V	I _F = 5A
		—	0.61	0.67	V	I _F = 10A
I _R ***	Cathode-To-Anode Leakage Current	—	5	30	μA	V _R = 80V
T _J , T _{STG}	Operating and Storage Temperature Range	-55°C to 150°C Max				

*** Pulse width < 300 uS, Duty cycle < 2%

Mechanical Data

Die Size	1905×1905	μm ²	CHIP DRAWING (Scribe Line is Excluded) 
Source Pad Size	1410×1410	μm ²	
Scribe Line Size	60	μm	
Wafer Diameter	6	in	
Wafer Thickness	250	μm	
Estimated Gross Die	4387(Yield>98%)		
Anode Metal Thickness	AlSiCu(5.5um)		
Cathode Metal Thickness	Ti\Ni\Ag(0.2um\0.3um\2um)		
Recommended Storage Environment	Store in original container, in dry nitrogen, < 6 months at an ambient temperature of 23°C±3°C >		

* Electrical characteristics are reported for the reference packaged part (TO-220) and can not be guaranteed in die sales form.

** Electrical characteristics are reported for the bare die. Variations in customer packaging materials, dimensions and processes may affect parametric performance.